

In re Appln. of Takayuki HISAKA
Application No. Unassigned

ABSTRACT AMENDMENTS

Replace the Abstract with:

A semiconductor device includes a semiconductor substrate ~~10~~, a channel layer ~~7~~, a Schottky layer ~~5a, 5b~~, a first layer ~~12~~ having a narrower band gap than the Schottky layer, a second layer ~~11~~ having band discontinuity with the Schottky layer, a gate electrode ~~1~~, an n⁺ layer ~~4~~, a source electrode ~~2~~, and a drain electrode ~~3~~. The first and second layers are ~~inserted in~~ within the Schottky layer, and the second layer is disposed on the first layer.